Freescale Semiconductor - KMPC8548EVUAUJ Datasheet

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=kmpc8548evuauj

  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^{2}C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^{2}C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^{2}C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^{2}C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)

        - VRRP and HSRP support for seamless router fail-over
        - Up to 16 exact-match MAC addresses supported
        - Broadcast address (accept/reject)
        - Hash table match on up to 512 multicast addresses
        - Promiscuous mode
    - Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
    - RMON statistics support
    - 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
    - MII management interface for control and status
    - Ability to force allocation of header information and buffer descriptors into L2 cache
- OCeaN switch fabric
    - Full crossbar packet switch
    - Reorders packets from a source based on priorities
    - Reorders packets to bypass blocked packets
    - Implements starvation avoidance algorithms
    - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
    - Four-channel controller
    - All channels accessible by both the local and remote masters
    - Extended DMA functions (advanced chaining and striding capability)
    - Support for scatter and gather transfers
    - Misaligned transfer capability
    - Interrupt on completed segment, link, list, and error
    - Supports transfers to or from any local memory or I/O port
    - Selectable hardware-enforced coherency (snoop/no snoop)
    - Ability to start and flow control each DMA channel from external 3-pin interface
    - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
    - PCI 2.2 and PCI-X 1.0 compatible
    - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
    - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
    - Host and agent mode support
    - 64-bit dual address cycle (DAC) support
    - PCI-X supports multiple split transactions
    - Supports PCI-to-memory and memory-to-PCI streaming

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, “FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications,” for details on the recommended operating conditions per protocol.
4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage		AV_{DD}	1.1 V ± 55 mV	V	1
Core power supply for SerDes transceivers		SV_{DD}	1.1 V ± 55 mV	V	—
Pad power supply for SerDes transceivers		XV_{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	—	4
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	3
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
Input voltage	DDR and DDR2 DRAM signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR and DDR2 DRAM reference	MV_{REF}	GND to $GV_{DD}/2$	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

4 Input Clocks

This section discusses the timing for the input clocks.

4.1 System Clock Timing

The following table provides the system clock (SYSCLK) AC timing specifications for the device.

Table 5. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV_{DD} = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	16	—	133	MHz	1, 6, 7, 8
SYSCLK cycle time	t_{SYSCLK}	7.5	—	60	ns	6, 7, 8
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies.See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The SYSCLK driver’s closed loop jitter bandwidth must be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
6. This parameter has been adjusted slower according to the workaround for device erratum GEN 13.
7. For spread spectrum clocking. Guidelines are + 0% to –1% down spread at modulation rate between 20 and 60 kHz on SYSCLK.
8. System with operating core frequency less than 1200 MHz must limit SYSCLK frequency to 100 MHz maximum.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal must be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that GV_{DD}(typ) = 2.5 V for DDR SDRAM, and GV_{DD}(typ) = 1.8 V for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.125$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[*n*] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This is typically set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8548E PowerQUICC III Integrated Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe must be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[*n*] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

> For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 3 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

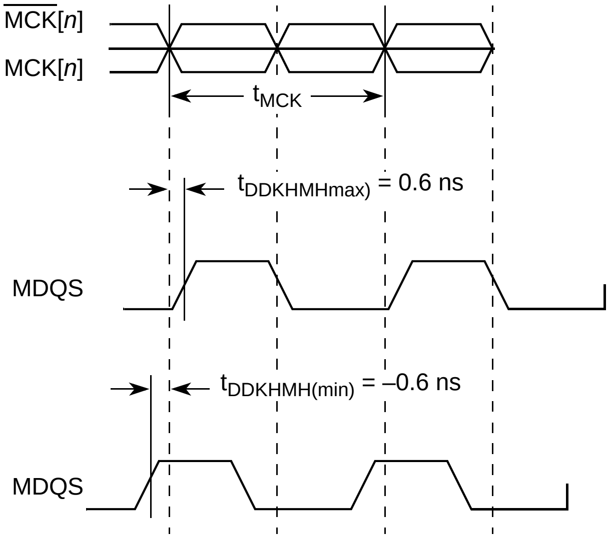


Figure 3. Timing Diagram for tDDKHMH

Figure 13 shows the MII receive AC timing diagram.

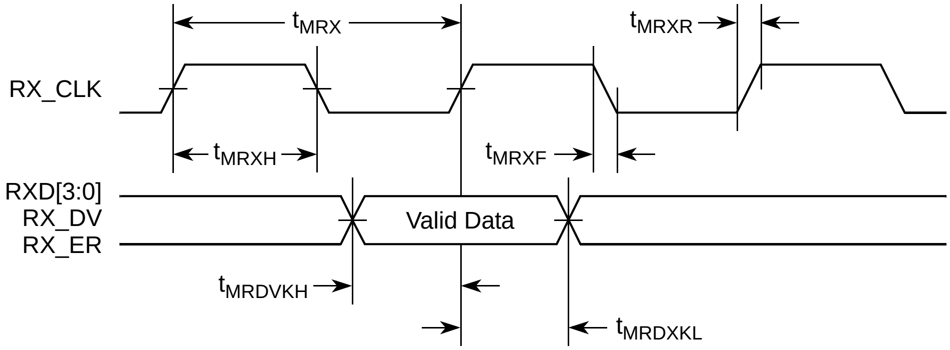


Figure 13. MII Receive AC Timing Diagram

8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 30. TBI Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TCG[9:0] setup time GTX_CLK going high	t_{TTKHDV}	2.0	—	—	ns
TCG[9:0] hold time from GTX_CLK going high	t_{TTKHDX}	1.0	—	—	ns
GTX_CLK rise (20%–80%)	t_{TTXR}[2]	—	—	1.0	ns
GTX_CLK fall time (80%–20%)	t_{TTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

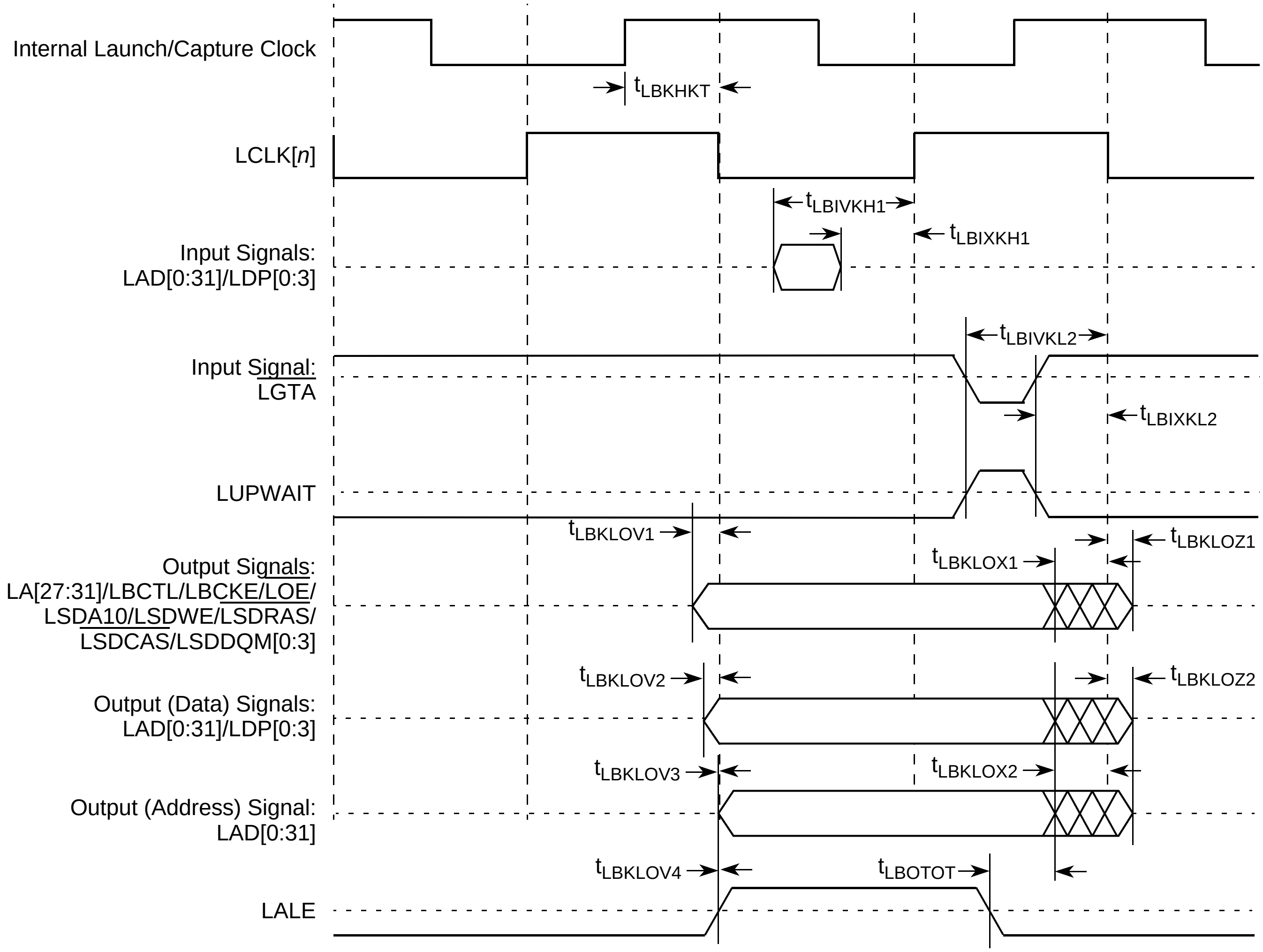


Figure 24. Local Bus Signals (PLL Bypass Mode)

NOTE

In PLL bypass mode, LCLK[*n*] is the inverted version of the internal clock with the delay of t_{LBKHKT}. In this mode, signals are launched at the rising edge of the internal clock and are captured at falling edge of the internal clock with the exception of $\overline{\text{LGTA}}$/LUPWAIT (which is captured on the rising edge of the internal clock).

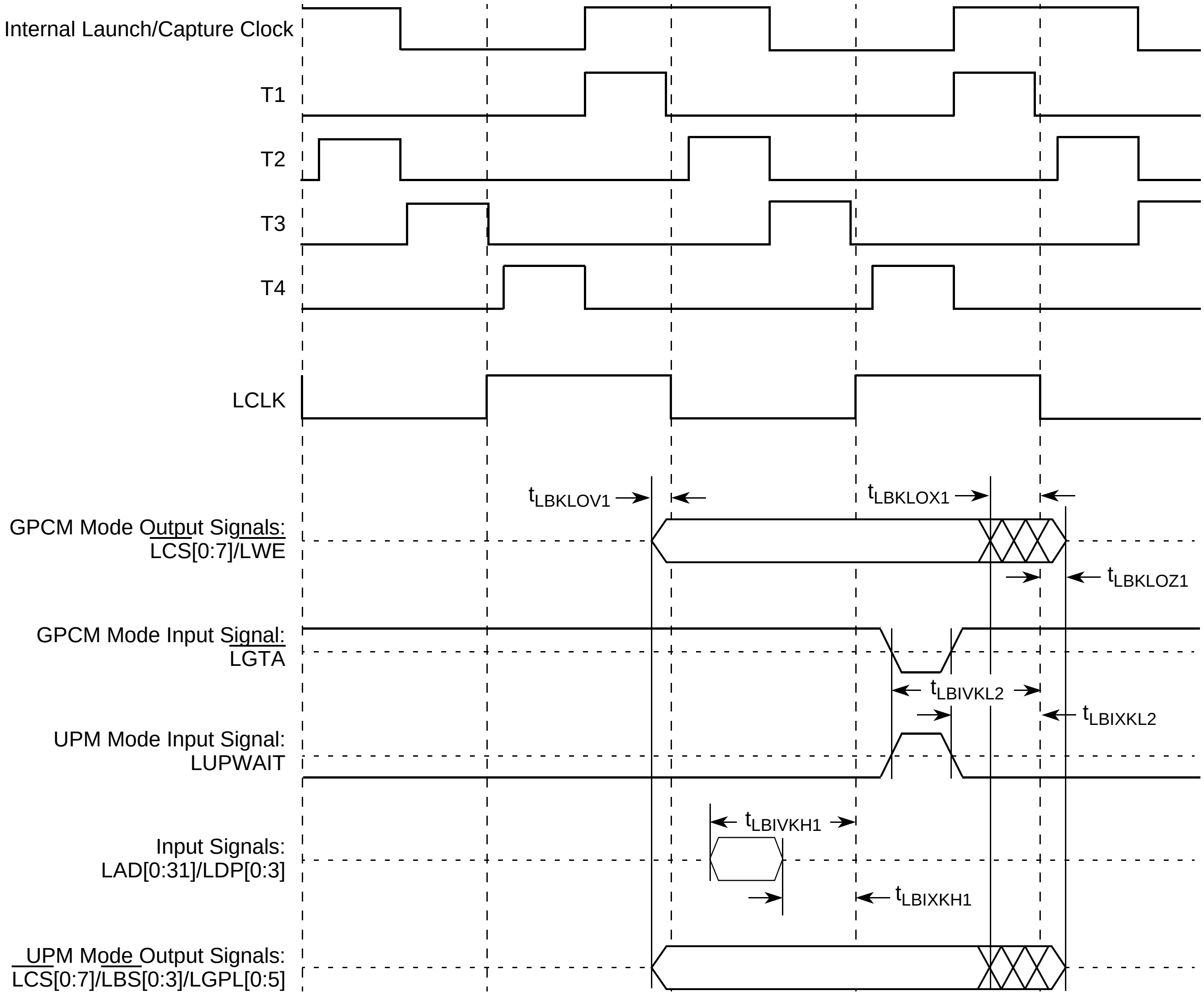


Figure 28. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

Table 43. JTAG DC Electrical Characteristics

Parameter	Symbol[1]	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or $V_{IN} = V_{DD}$)	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN}.

12.2 JTAG AC Electrical Specifications

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 32.

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)[1]

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	6
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times:				ns	4
Boundary-scan data	t_{JTDVKH}	4	—		
TMS, TDI	t_{JTIVKH}	0	—		
Input hold times:				ns	4
Boundary-scan data	t_{JTDXKH}	20	—		
TMS, TDI	t_{JTIXKH}	25	—		

Figure 34 shows the AC timing diagram for the I^2C bus.

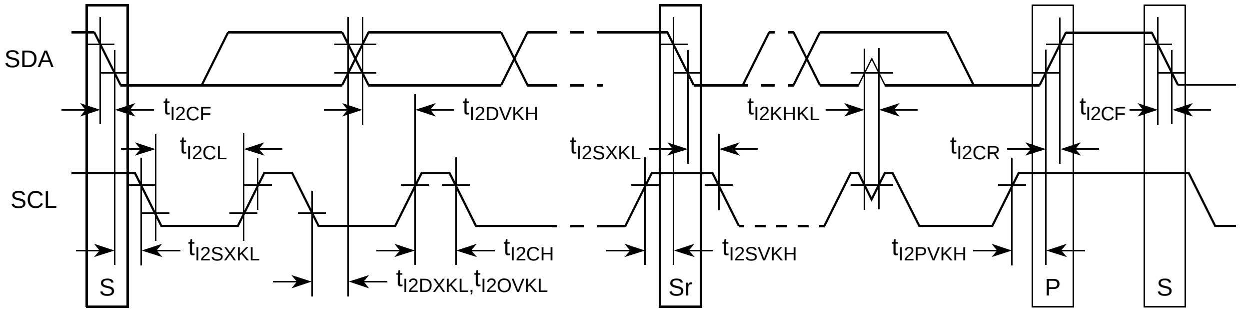


Figure 34. I^2C Bus AC Timing Diagram

Table 50. GP_{IN} DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5 V	BV_{DD}	2.37	2.63	V
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IH}	—	10	μA

Note:

1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

15 PCI/PCI-X

This section describes the DC and AC electrical specifications for the PCI/PCI-X bus of the device.

Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

15.1 PCI/PCI-X DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI/PCI-X interface.

Table 51. PCI/PCI-X DC Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	2
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V	—

Notes:

1. Ranges listed do not meet the full range of the DC specifications of the *PCI 2.2 Local Bus Specifications*.
2. The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

15.2 PCI/PCI-X AC Electrical Specifications

This section describes the general AC timing parameters of the PCI/PCI-X bus. Note that the clock reference CLK is represented by SYSCLK when the PCI controller is configured for synchronous mode and by PCI*n*_CLK when it is configured for asynchronous mode.

802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE Std. 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

18.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (baud frequency)/1667 is applied to the jitter. The data pattern for template measurements is the continuous jitter test pattern (CJPAT) defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. The amount of data represented in the eye shall be adequate to ensure that the bit error ratio is less than 10^{-12}. The eye pattern shall be measured with AC coupling and the compliance template centered at 0 V differential. The left and right edges of the template shall be aligned with the mean zero crossing points of the measured data eye. The load for this test shall be 100-Ω resistive ± 5% differential to 2.5 GHz.

18.9.2 Jitter Test Measurements

For the purpose of jitter measurement, the effects of a single-pole high pass filter with a 3 dB point at (baud frequency)/1667 is applied to the jitter. The data pattern for jitter measurements is the Continuous Jitter test pattern (CJPAT) pattern defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. Jitter shall be measured with AC coupling and at 0 V differential. Jitter measurement for the transmitter (or for calibration of a jitter tolerance setup) shall be performed with a test procedure resulting in a BER curve such as that described in Annex 48B of IEEE 802.3ae.

18.9.3 Transmit Jitter

Transmit jitter is measured at the driver output when terminated into a load of 100 Ω resistive ± 5% differential to 2.5 GHz.

18.9.4 Jitter Tolerance

Jitter tolerance is measured at the receiver using a jitter tolerance test signal. This signal is obtained by first producing the sum of deterministic and random jitter defined in Section 18.7, “Receiver Specifications,” and then adjusting the signal amplitude until the data eye contacts the 6 points of the minimum eye opening of the receive template shown in Figure 54 and Table 69. Note that for this to occur, the test signal must have vertical waveform symmetry about the average value and have horizontal symmetry (including jitter) about the mean zero crossing. Eye template measurement requirements are as defined above. Random jitter is calibrated using a high pass filter with a low frequency corner at 20 MHz and a 20 dB/decade roll-off below this. The required sinusoidal jitter specified in Section 18.7, “Receiver Specifications,” is then added to the signal and the test load is replaced by the receiver being tested.

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
I^{2}C interface				
IIC1_SCL	AG22	I/O	OV$_{DD}$	4, 27
IIC1_SDA	AG21	I/O	OV$_{DD}$	4, 27
IIC2_SCL	AG15	I/O	OV$_{DD}$	4, 27
IIC2_SDA	AG14	I/O	OV$_{DD}$	4, 27
SerDes				
SD_RX[0:7]	M28, N26, P28, R26, W26, Y28, AA26, AB28	I	XV$_{DD}$	—
$\overline{\text{SD\_RX}}$[0:7]	M27, N25, P27, R25, W25, Y27, AA25, AB27	I	XV$_{DD}$	—
SD_TX[0:7]	M22, N20, P22, R20, U20, V22, W20, Y22	O	XV$_{DD}$	—
$\overline{\text{SD\_TX}}$[0:7]	M23, N21, P23, R21, U21, V23, W21, Y23	O	XV$_{DD}$	—
SD_PLL_TPD	U28	O	XV$_{DD}$	24
SD_REF_CLK	T28	I	XV$_{DD}$	3
$\overline{\text{SD\_REF\_CLK}}$	T27	I	XV$_{DD}$	3
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV$_{DD}$	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV$_{DD}$	—
$\overline{\text{HRESET\_REQ}}$	AG16	O	OV$_{DD}$	29
$\overline{\text{SRESET}}$	AG20	I	OV$_{DD}$	—
$\overline{\text{CKSTP\_IN}}$	AA9	I	OV$_{DD}$	—
$\overline{\text{CKSTP\_OUT}}$	AA8	O	OV$_{DD}$	2, 4
Debug				
TRIG_IN	AB2	I	OV$_{DD}$	—
TRIG_OUT/READY/$\overline{\text{QUIESCE}}$	AB1	O	OV$_{DD}$	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV$_{DD}$	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV$_{DD}$	6, 19, 29
MDVAL	AE5	O	OV$_{DD}$	6
CLK_OUT	AE21	O	OV$_{DD}$	11

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—

Table 72 provides the pin-out listing for the MPC8547E 783 FC-PBGA package.

NOTE

All note references in the following table use the same numbers as those for Table 71. See Table 71 for the meanings of these notes.

Table 72. MPC8547E Pinout Listing

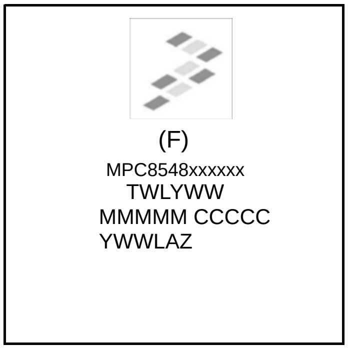
Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1 (One 64-Bit or One 32-Bit)				
PCI1_AD[63:32]	AB14, AC15, AA15, Y16, W16, AB16, AC16, AA16, AE17, AA18, W18, AC17, AD16, AE16, Y17, AC18, AB18, AA19, AB19, AB21, AA20, AC20, AB20, AB22, AC22, AD21, AB23, AF23, AD23, AE23, AC23, AC24	I/O	OV_{DD}	17
PCI1_AD[31:0]	AH6, AE7, AF7, AG7, AH7, AF8, AH8, AE9, AH9, AC10, AB10, AD10, AG10, AA10, AH10, AA11, AB12, AE12, AG12, AH12, AB13, AA12, AC13, AE13, Y14, W13, AG13, V14, AH13, AC14, Y15, AB15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[7:4]	AF15, AD14, AE15, AD15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[3:0]	AF9, AD11, Y12, Y13	I/O	OV_{DD}	17
PCI1_PAR64	W15	I/O	OV_{DD}	—
$\overline{\text{PCI1\_GNT}}$[4:1]	AG6, AE6, AF5, AH5	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI1\_GNT0}}$	AG5	I/O	OV_{DD}	—
$\overline{\text{PCI1\_IRDY}}$	AF11	I/O	OV_{DD}	2
PCI1_PAR	AD12	I/O	OV_{DD}	—
$\overline{\text{PCI1\_PERR}}$	AC12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_SERR}}$	V13	I/O	OV_{DD}	2, 4
$\overline{\text{PCI1\_STOP}}$	W12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ64}}$	AF14	I/O	OV_{DD}	2, 5,10
$\overline{\text{PCI1\_ACK64}}$	V15	I/O	OV_{DD}	2
Reserved	AE28	—	—	2
Reserved	AD26	—	—	2
Reserved	AD25	—	—	2

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	AE26	—	—	2
cfg_pci1_clk	AG24	I	OV$_{\text{DD}}$	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	2
Reserved	AG25	—	—	2
Reserved	AD24	—	—	2
Reserved	AF24	—	—	2
Reserved	AD27	—	—	2
Reserved	AD28, AE27, W17, AF26	—	—	2
Reserved	AH25	—	—	2
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV$_{\text{DD}}$	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV$_{\text{DD}}$	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV$_{\text{DD}}$	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV$_{\text{DD}}$	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV$_{\text{DD}}$	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV$_{\text{DD}}$	—
MBA[0:2]	F7, J7, M11	O	GV$_{\text{DD}}$	—
$\overline{\text{MWE}}$	E7	O	GV$_{\text{DD}}$	—
$\overline{\text{MCAS}}$	H7	O	GV$_{\text{DD}}$	—
$\overline{\text{MRAS}}$	L8	O	GV$_{\text{DD}}$	—
MCKE[0:3]	F10, C10, J11, H11	O	GV$_{\text{DD}}$	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV$_{\text{DD}}$	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV$_{\text{DD}}$	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV$_{\text{DD}}$	—
MODT[0:3]	E6, K6, L7, M7	O	GV$_{\text{DD}}$	—
MDIC[0:1]	A19, B19	I/O	GV$_{\text{DD}}$	36

23.2 Part Marking

Parts are marked as the example shown in Figure 64.



Notes:

TWLYYWW is final test traceability code.
MMMMM is 5 digit mask number.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.
YWWLAZ is assembly traceability code.

Figure 64. Part Marking for CBGA and PBGA Device

24 Document Revision History

The following table provides a revision history for this hardware specification.

Table 88. Document Revision History

Rev. Number	Date	Substantive Change(s)
9	02/2012	• Updated Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid," with version 3.0 silicon information. • Added Figure 56, "Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA with Stamped Lid." • Updated Table 87, "Part Numbering Nomenclature," with version 3.0 silicon information. • Removed Note from Section 5.1, "Power-On Ramp Rate". • Changed the Table 10 title to "Power Supply Ramp Rate". • Removed table 11. • Updated the title of Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid" to include Thermal Version 2.1.3 and Version 3.1.x Silicon. • Corrected the leaded Solder Ball composition in Table 70, "Package Parameters" • Updated Table 87, "Part Numbering Nomenclature," with Version 3.1.x silicon information. • Updated the Min and Max value of TDO in the valid times row of Table 44, "JTAG AC Timing Specifications (Independent of SYSCLK)[1]" from 4 and 25 to 2 and 10 respectively .
8	04/2011	• Added Section 14.1, "GPOUT/GPIN Electrical Characteristics." • Updated Table 71, "MPC8548E Pinout Listing," Table 72, "MPC8547E Pinout Listing," Table 73, "MPC8545E Pinout Listing," and Table 74, "MPC8543E Pinout Listing," to reflect that the TDO signal is not driven during HRSET* assertion. • Updated Table 87, "Part Numbering Nomenclature" with Ver. 2.1.3 silicon information.
7	09/2010	• In Table 37, "MII Management AC Timing Specifications, modified the fifth row from "MDC to MDIO delay tMDKHDX (16 × tptb_clk × 8) – 3 — (16 × tptb_clk × 8) + 3" to "MDC to MDIO delay tMDKHDX (16 × tCCB × 8) – 3 — (16 × tCCB × 8) + 3." • Updated Figure 55, "Mechanical Dimensions and Bottom Surface Nomenclature of the HiCTE FC-CBGA and FC-PBGA with Full Lid and figure notes.
6	12/2009	• In Section 5.1, "Power-On Ramp Rate" added explanation that Power-On Ramp Rate is required to avoid falsely triggering ESD circuitry. • In Table 13 changed required ramp rate from 545 V/s for MVREF and VDD/XVDD/SVDD to 3500 V/s for MVREF and 4000 V/s for VDD. • In Table 13 deleted ramp rate requirement for XVDD/SVDD. • In Table 13 footnote 1 changed voltage range of concern from 0–400 mV to 20–500mV. • In Table 13 added footnote 2 explaining that VDD voltage ramp rate is intended to control ramp rate of AVDD pins.
5	10/2009	• In Table 27, "GMII Receive AC Timing Specifications," changed duty cycle specification from 40/60 to 35/75 for RX_CLK duty cycle. • Updated tMDKHDX in Table 37, "MII Management AC Timing Specifications." • Added a reference to Revision 2.1.2. • Updated Table 55, "MII Management AC Timing Specifications." • Added Section 5.1, "Power-On Ramp Rate."